**DUAL P-CHANNEL MOSFET** 

–12 V, –4.0 A, 67 mΩ

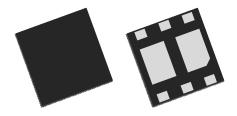
### Description

The  $\mu$ PA2672T1R is Dual P-channel MOS Field Effect Transistors for switching application.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

# Features

- -1.8V drive available
- Low on-state resistance
  - ----  $R_{DS(on)1} = 67 \text{ m}\Omega \text{ MAX}. (V_{GS} = -4.5 \text{ V}, I_D = -2.0 \text{ A})$
  - ----  $R_{DS (on)2} = 92 \text{ m}\Omega \text{ MAX.}$  ( $V_{GS} = -2.5 \text{ V}$ ,  $I_D = -2.0 \text{ A}$ )
  - ----  $R_{DS (on)3} = 159 \text{ m}\Omega \text{ MAX}. (V_{GS} = -1.8 \text{ V}, I_D = -2.0 \text{ A})$
- Built-in gate protection diode
- Lead-free and Halogen-free



6pinHUSON2020(Dual)

### **Ordering Information**

Part Number	Package		
μPA2672T1R-E2-AX* <sup>1</sup>	6pinHUSON2020		

Note: \*1. Pb-free (This product does not contain Pb in the external electrode and other parts.)

# Absolute Maximum Ratings (T<sub>A</sub> = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ( $V_{GS} = 0 V$ )	V <sub>DSS</sub>	-12	V
Gate to Source Voltage ( $V_{DS} = 0 V$ )	V <sub>GSS</sub>	<b>∓10</b>	V
Drain Current (DC)	I <sub>D(DC)</sub>	∓4.0	А
Drain Current (pulse) *1	I <sub>D(pulse)</sub>	∓16	А
Total Power Dissipation (1 unit, 5 s) *2	P <sub>T1</sub>	1.5	W
Total Power Dissipation (2 units, 5 s) *2	P <sub>T2</sub>	2.3	W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C

Notes: \*1. PW $\leq$ 10  $\mu$ s, Duty Cycle $\leq$ 1%

\*2. Mounted on glass epoxy board of 25.4mm x 25.4mm x 0.8mmt

Data Sheet

Rev.1.01 Apr 15, 2013

# **Electrical Characteristics (T<sub>A</sub> = 25°C)**

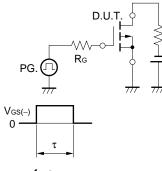
Characteristics	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			-1.0	μA	$V_{DS} = -12 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	
Gate Leakage Current	I <sub>GSS</sub>			<b>∓10</b>	μA	V <sub>GS</sub> = ∓8 V, V <sub>DS</sub> = 0 V	
Gate Cut-off Voltage	V <sub>GS(off)</sub>	-0.4		-1.1	V	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	
Forward Transfer Admittance *1	y <sub>fs</sub>	4.5			S	$V_{DS} = -5 \text{ V}, \text{ I}_{D} = -2.0 \text{ A}$	
Drain to Source On-state	R <sub>DS(on)1</sub>		52	67	mΩ	$V_{GS}$ = -4.5 V, $I_D$ = -2.0 A	
Resistance *1	R <sub>DS(on)2</sub>		68	92	mΩ	$V_{GS}$ = -2.5 V, $I_D$ = -2.0 A	
	R <sub>DS(on)3</sub>		95	159	mΩ	$V_{GS} = -1.8 \text{ V}, I_D = -2.0 \text{ A}$	
Input Capacitance	C <sub>iss</sub>		486		pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$	
Output Capacitance	C <sub>oss</sub>		108		pF	f = 1.0 MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		82		pF		
Turn-on Delay Time	t <sub>d (on)</sub>		11.5		ns	$I_{D} = -2.0 \text{ A}, V_{DD} = -6 \text{ V}, \\ V_{GS} = -4.0 \text{ V}, R_{G} = 6 \Omega$	
Rise Time	tr		3.5		ns		
Turn-off Delay Time	t <sub>d (off)</sub>		24.0		ns		
Fall Time	t <sub>f</sub>		20.0		ns		
Total Gate Charge	Q <sub>G</sub>		5.0		nC	$I_D = -4.0 \text{ A}$ , $V_{DD} = -9.6 \text{ V}$ ,	
Gate to Source Charge	Q <sub>GS</sub>		1.0		nC	V <sub>GS</sub> = -4.5 V	
Gate to Drain Charge	Q <sub>GD</sub>		1.3		nC	1	
Body Diode Forward Voltage *1	V <sub>F(S-D)</sub>			1.5	V	$I_F = 4.0 \text{ A}, V_{GS} = 0 \text{ V}$	

Note: \*1. Pulsed

### **TEST CIRCUIT 1 SWITCHING TIME**

R

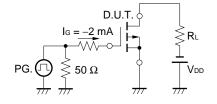
Vdd



 $\tau = 1 \,\mu s$ Duty Cycle  $\leq 1\%$ 

#### Vgs(-) VGS Wave Form 0 10% 90% Vgs VDS(-) 90% 90% Vds V<sub>DS</sub> Wave Form 10% 10% 0 tr tſ td(on) td(off) tor toff

### TEST CIRCUIT 2 GATE CHARGE

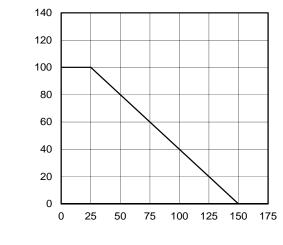


dT - Percentage of Rated Power - %

I<sub>D</sub> – Drain Current - A

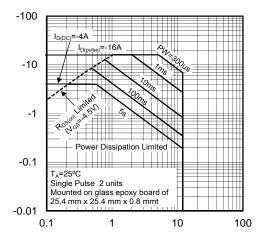
# Typical Characteristics $(T_A = 25^{\circ}C)$

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

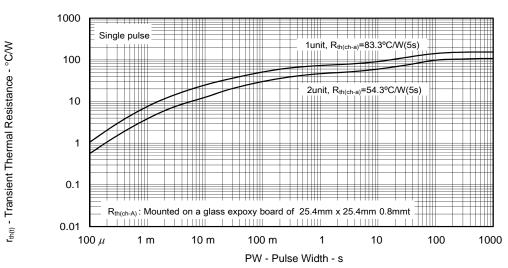


T<sub>A</sub> -Ambient Temperature - °C



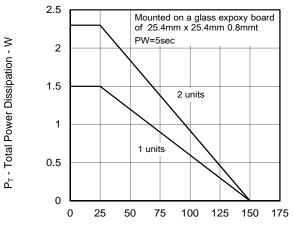


 $V_{\mbox{\scriptsize DS}}$  - Drain to Source Voltage - V



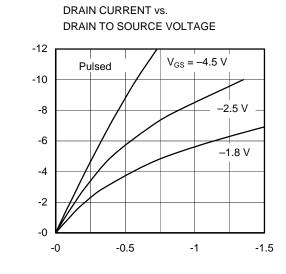
### TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE

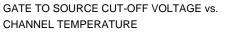


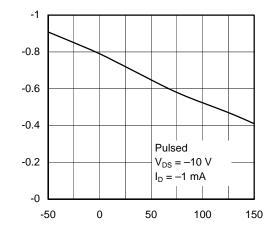
T<sub>A</sub> -Ambient Temperature - °C



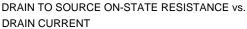




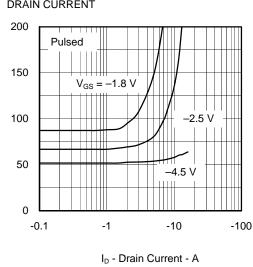




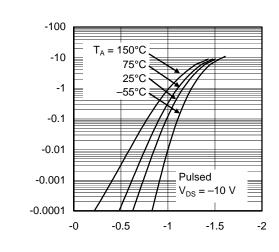
T<sub>ch</sub> - Channel Temperature - °C







FORWARD TRANSFER CHARACTERISTICS



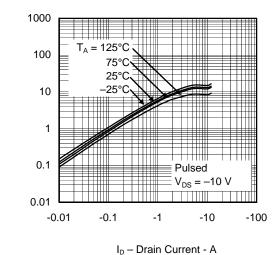
Ip - Drain Current - A

| y<sub>fs</sub> | - Forward Transfer Admittance - S

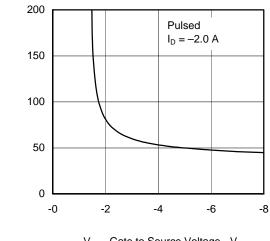
 $R_{\text{DS(on)}}$  – Drain to Source On-state Resistance -  $m\Omega$ 

V<sub>GS</sub> - Gate to Source Voltage - V

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

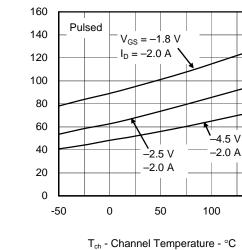


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



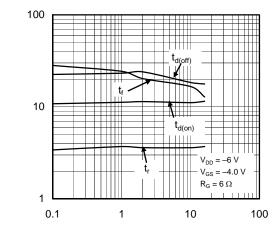
I<sub>D</sub> –Drain Current - A

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

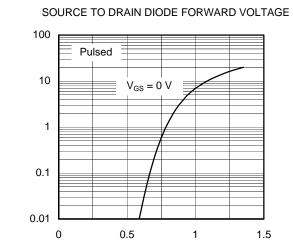


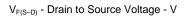
#### SWITCHING CHARACTERISTICS

150

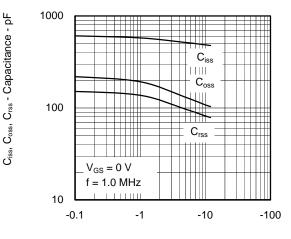


I<sub>D</sub> - Drain Current - A



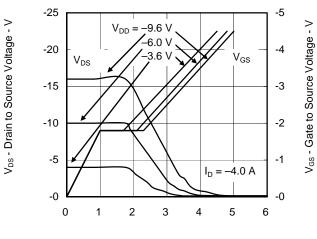


CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



 $V_{\text{DS}}$  – Drain to Source Voltage - V

DYNAMIC INPUT/OUTPUT CHARACTERISTICS

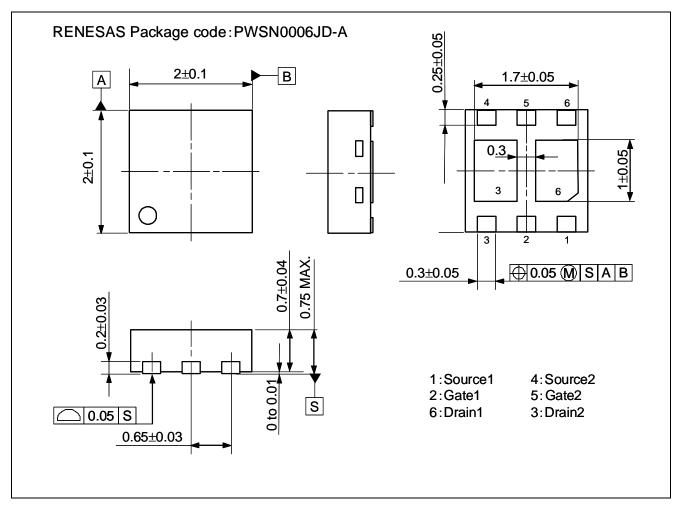


Q<sub>G</sub> - Gate Charge - nC

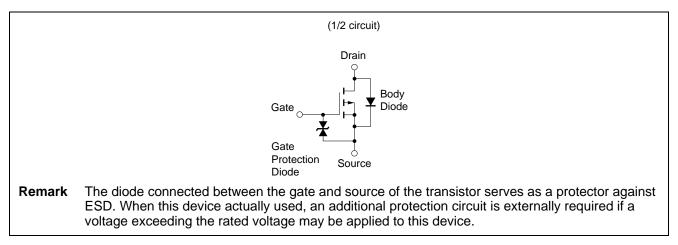
IF - Diode Forward Current – A

# Package Drawings (Unit: mm)

### 6pinHUSON2020



# **Equivalent Circuit**



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